



JST41 Series 40A TRIACs

Rev.4.0

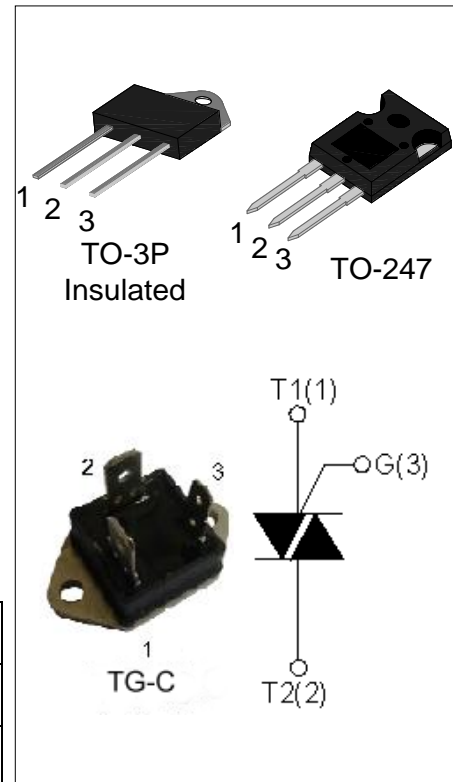
DESCRIPTION:

JST41 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

JST41Z provides insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	600 and 800 and 1200 and 1600	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600/800/1200/1600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600/800/1200/1600	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-3P(Ins) ($T_C=80^\circ\text{C}$)	$I_{T(RMS)}$	40	A
	TO-247/ TG-C ($T_C=90^\circ\text{C}$)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	400	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	880	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	50	$\text{A}/\mu\text{s}$

Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	50	mA
V_{GT}		I - II -III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	80	mA
		II		100	
I_H	$I_T=100\text{mA}$		MAX	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	1000	V/ μs
(dV/dt)c	Without snubber $T_j=125^{\circ}\text{C}$		MIN	20	V/ μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	50	mA
		IV		70	
V_{GT}		ALL	MAX	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III-IV	MAX	90	mA
		II		100	
I_H	$I_T=100\text{mA}$		MAX	80	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	500	V/ μs
(dV/dt)c	Without snubber $T_j=125^{\circ}\text{C}$		MIN	30	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=60A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.55	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	10	μA
I_{RRM}		$T_j=125^\circ C$	5	mA

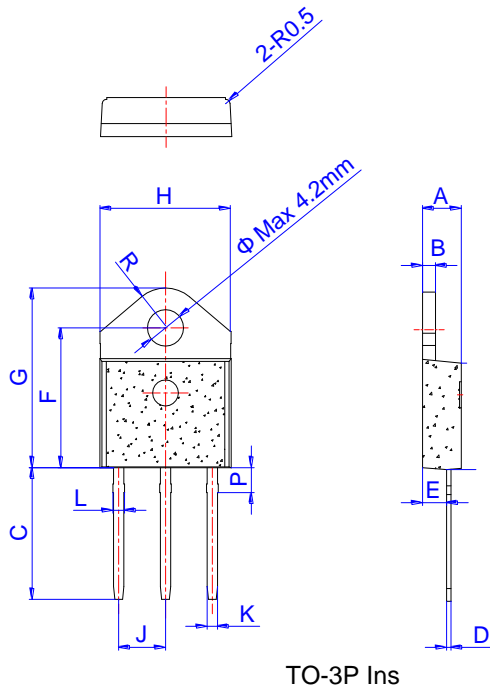
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-3P(Ins)	0.9	$^\circ C/W$
		TO-247/ TG-C	0.8	

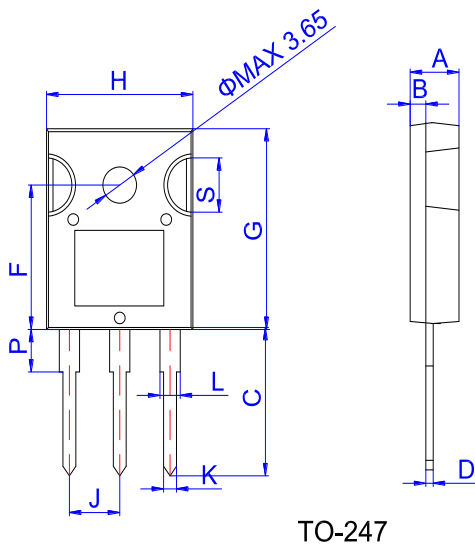
ORDERING INFORMATION

JieJie Microelectronics Co.,Ltd J ST 41 Z -600 BW	BW: $I_{GT3} \leq 50mA$ B: $I_{GT1-3} \leq 50mA$ $I_{GT4} \leq 70mA$ 600: $V_{DRM} / V_{RRM} \geq 600V$ 800: $V_{DRM} / V_{RRM} \geq 800V$ 1200: $V_{DRM} / V_{RRM} \geq 1200V$ 1600: $V_{DRM} / V_{RRM} \geq 1600V$
	Triacs $I_{T(RMS)}: 40A$ Z: TO-3P(Ins) S: TO-247 T: TG-C

PACKAGE MECHANICAL DATA

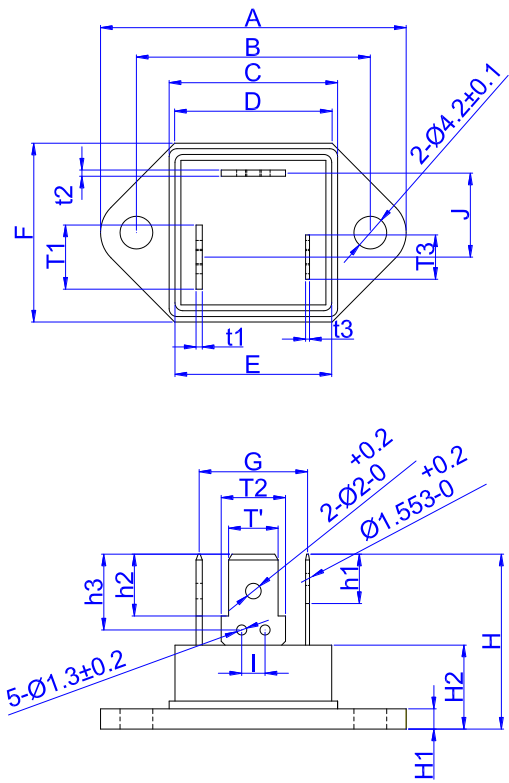


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.9		5.4	0.193		0.213
B	1.6		2.0	0.063		0.079
C	14.35		15.4	0.565		0.606
D	0.5		0.8	0.020		0.031
F	14.4		15.1	0.567		0.594
G	19.7		20.6	0.775		0.811
H	15.4		16.2	0.606		0.638
J	5.3		5.6	0.209		0.220
K	1.3		1.5	0.051		0.059
L	2.8		3.3	0.110		0.130
P	3.7		4.2	0.146		0.165
S	5.35		5.65	0.211		0.222

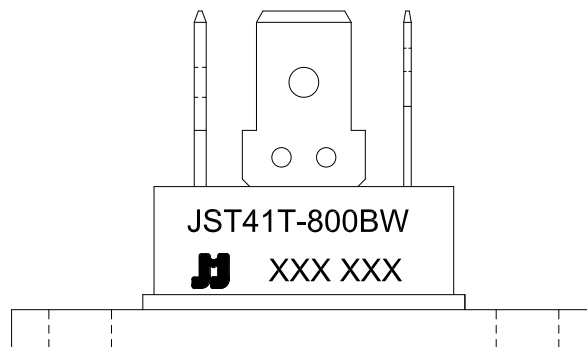
PACKAGE MECHANICAL DATA



TG-C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			39.2			1.543
B	29.8	30.0	30.2	1.173	1.181	1.189
C			21.6			0.85
D			20.2			0.795
E			20.5			0.791
F			23			0.906
T1、T2		8.10			0.318	
T3		5.65			0.222	
T'		6.35			0.25	
t1、t2		0.8			0.031	
t3		0.6			0.023	
G		13.9			0.547	
H1		2.6			0.102	
H2		10.8			0.425	
H			22.8			0.886
h1	6.2	6.35	6.5	0.244	0.25	0.256
h2	7.8	7.95	8.1	0.307	0.313	0.319
h3	9.45	9.75	10.05	0.372	0.384	0.396
I	2.7	3.0	3.3	0.106	0.118	0.130
J		10.8			0.425	

MARKING



TG-C marking

FIG.1 Maximum power dissipation versus RMS on-state current

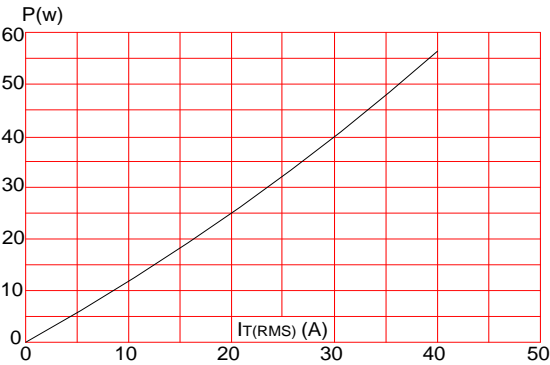


FIG.3: Surge peak on-state current versus number of cycles

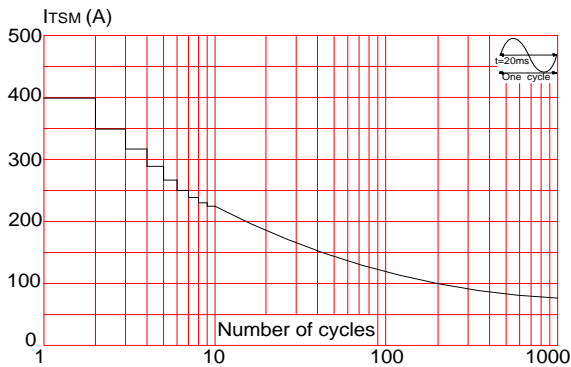


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

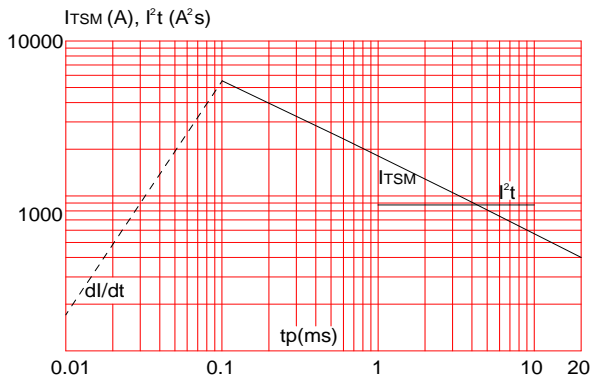


FIG.2: RMS on-state current versus case temperature

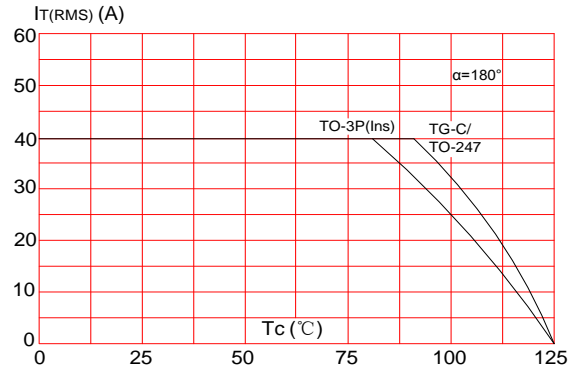


FIG.4: On-state characteristics (maximum values)

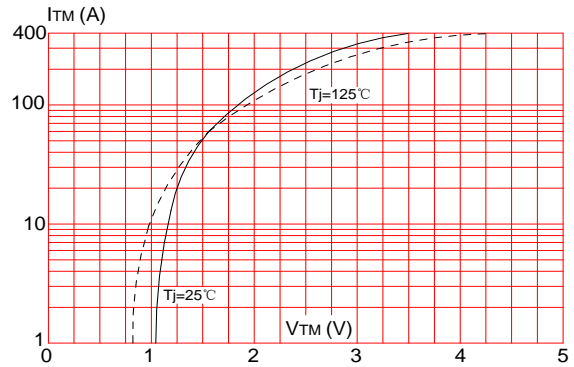
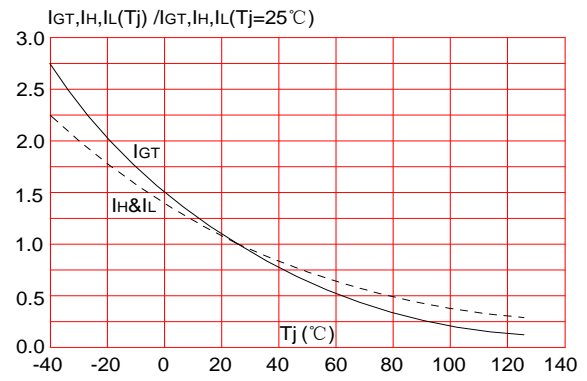



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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